

Schottky barrier diode

RB715W / RB715F

●Applications

General purpose detection
High speed switching

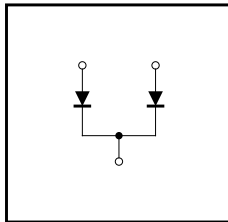
●Features

- 1) Small surface mounting type (EMD3, UMD3)
- 2) Low V_F and low I_R
- 3) High reliability

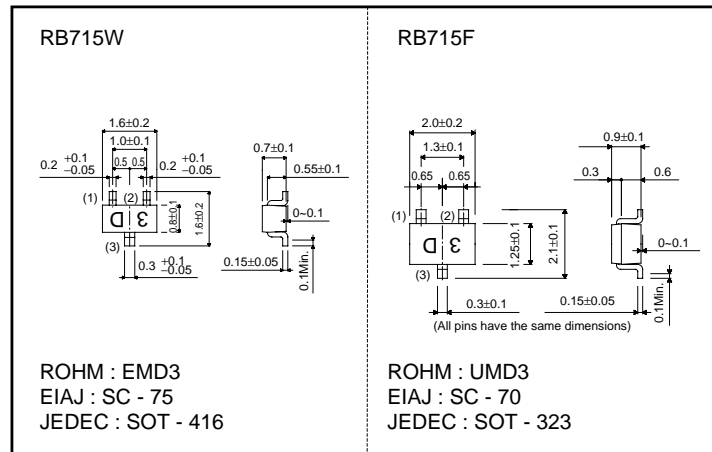
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	30	mA
Peak forward surge current*	I_{FSM}	200	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	$I_F=1mA$
Reverse current	I_R	-	-	1	μA	$V_R=10V$
Capacitance between terminals	C_T	-	2.0	-	pF	$V_R=1V, f=1MHz$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta=25°C)

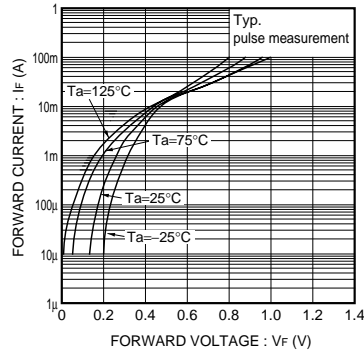


Fig. 1 Forward characteristics

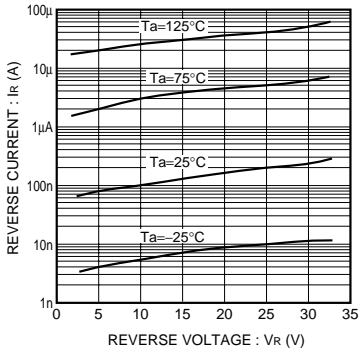


Fig. 2 Reverse characteristics

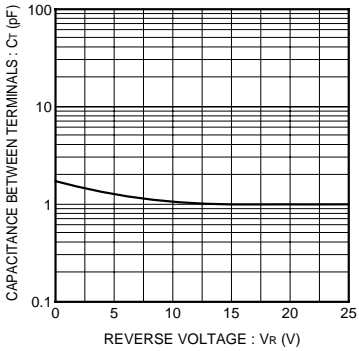


Fig. 3 Capacitance between terminals characteristics

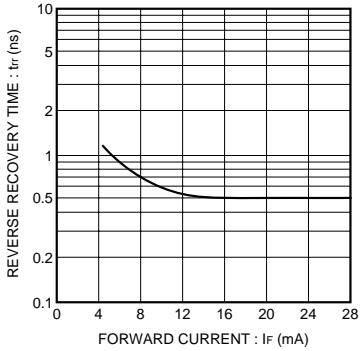


Fig. 4 Reverse recovery time characteristics